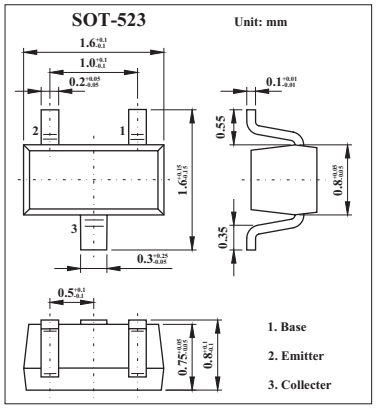
Low Frequency Transistor

2SC5585



Features

- Hig current.
- Low $V_{CE(sat)}$:$V_{CE(sat)}$≤250mV at I_C=200mA/I_B=10mA

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature range	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C = 10μA	15			V
Collectoe-emitter brakdown voltage	V_{CEO}	I_C = 1mA	12			V
Emitter-base breakdown voltage	V_{EBO}	I_E = 10μA	6			V
Collector cut-off current	I_{CBO}	V_{CB}=15 V			100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= 6 V			100	nA
DC current gain	h_{FE}	V_{CE}= 2 V, I_C = 10mA	270		680	
Collector emitter saturation voltage	$V_{CE(sat)}$	I_C=200mA,I_B=10mA		90	250	mV
Collector output capacitance	Cob	V_{CB}=10V,I_E=0,f=1MHz		7.5		pF
Transition frequency	f_T	V_{CE} = 2V, I_E =-10mA,f=100MHz		320		MHz

Marking

Marking	BX